

LIST OF JOURNAL PAPERS 2014

- 1 - Alexandru, M., Florentin, M., Constant, A., Schmidt, B., Michel, P., Godignon, P.
" 5 MEV PROTON AND 15 MEV ELECTRON RADIATION EFFECTS STUDY ON 4H-SIC NMOSFET ELECTRICAL PARAMETERS "
IEEE TRANSACTIONS ON NUCLEAR SCIENCE. Vol.61 n° (4), 1732-1738, 2014.

- 2 - Alexandru, M., Banu, V., Florentin, M., Jordà, X., Vellvehí, M., Tournier, D.
" HIGH TEMPERATURE ELECTRICAL CHARACTERIZATION OF 4H-SIC MESFET BASIC LOGIC GATES"
MATERIALS SCIENCE FORUM. 15th International Conference on Silicon Carbide and Related Materials (ICSCRM 2013), SEP 29-OCT 04, 2013, Miyazaki, JAPAN. Vol.778-780 1130-1134, 2014.

- 3 - Altet, J., González, J.L., Gomez, D., Perpiñá, X., Claeys, W., Grauby, S., Dufis, C., Vellvehí, M., Mateo, D., Reverter, F., Dilhaire, S., Jordà, X.
" ELECTRO-THERMAL CHARACTERIZATION OF A DIFFERENTIAL TEMPERATURE SENSOR IN A 65 NM CMOS IC: APPLICATIONS TO GAIN MONITORING IN RF AMPLIFIERS "
MICROELECTRONICS JOURNAL. Vol.45 n° (5), 484-490, 2014.

- 4 - Banu, V., Montserrat, J., Alexandru, M., Jordà, X., Millán, J., Godignon, P.
" MONOLITHIC INTEGRATION OF POWER MESFET FOR HIGH TEMPERATURE SIC INTEGRATED CIRCUITS "
MATERIALS SCIENCE FORUM. 15th International Conference on Silicon Carbide and Related Materials (ICSCRM 2013), SEP 29-OCT 04, 2013, Miyazaki, JAPAN. Vol.778-780 891-894, 2014.

- 5 - Banu, V., Godignon, P., Alexandru, M., Montserrat, J., Jordà, X., Millán, J.
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ROMANIAN JOURNAL OF INFORMATION SCIENCE AND TECHNOLOGY. Vol.17 n° (4), 417-432, 2014.

- 6 - Bartolf, H., Sundaramoorthy, V., Mihaila, A., Berthou, M., Godignon, P., Millán, J.
" STUDY OF 4H-SIC SCHOTTKY DIODE DESIGNS FOR 3.3KV APPLICATIONS "
MATERIALS SCIENCE FORUM. 15th International Conference on Silicon Carbide and Related Materials (ICSCRM 2013), SEP 29-OCT 04, 2013, Miyazaki, JAPAN. Vol.778-780 795-799, 2014.

- 7 - Berthou, M., Godignon, P., Millán, J.
" MONOLITHICALLY INTEGRATED TEMPERATURE SENSOR IN SILICON CARBIDE POWER MOSFETS "
IEEE TRANSACTIONS ON POWER ELECTRONICS. Vol.29 n° (9), 4970-4977, 2014.

- 8 - Berthou, M., Godignon, P., Calvo, J., Mihaila, A., Bianda, E., Nistor, I.
" COMPARISON OF 5KV SIC JBS AND PIN DIODES "
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- 9 - Blázquez, O., López-Vidrier, J., Hernández, S., Montserrat, J., Garrido, B.
" ELECTRO-OPTICAL PROPERTIES OF NON-STOICHIOMETRIC SILICON NITRIDE FILMS FOR PHOTOVOLTAIC APPLICATIONS "
ENERGY PROCEDIA. Proceedings of E-MRS Spring Meeting 2013 Symposium D Advanced

Inorganic Materials and Structures for Photovoltaics 27-31 May 2013, Strasbourg, France. Vol.44 145-150, 2014.

10 - Florentin, M., Alexandru, M., Constant, A., Schmidt, B., Millán, J., Godignon, P.
" **LOW ENERGY PROTON RADIATION IMPACT ON 4H-SIC NMOSFET GATE OXIDE STABILITY** "
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11 - Florentin, M., Montserrat, J., Brosselard, P., Henry, A., Godignon, P.
" **RAPID THERMAL OXIDATION OF SI-FACE N AND P-TYPE ON-AXIS 4H-SIC** "
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12 - Jabakhanji, B., Consejo, C., Camara, N., Desrat, W., Godignon, P., Jouault, B.
" **QUANTUM HALL EFFECT OF SELF-ORGANIZED GRAPHENE MONOLAYERS ON THE C-FACE OF 6H-SIC** "
JOURNAL OF PHYSICS D-APPLIED PHYSICS. Vol.47 n° (9), 094009, 2014.

13 - León, J., Perpiñá, X., Vellvehí, M., Jordà, X., Berthou, M., Godignon, P.
" **SMALL SIGNAL THERMAL ANALYSIS OF LOCAL MULTIBARRIER BEHAVIOUR IN SIC SCHOTTKY DIODES** "
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14 - León, J., Berthou, M., Perpiñá, X., Banu, V., Montserrat, J., Vellvehí, M., Godignon, P., Jordà, X.
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16 - Menéndez, E., Hynowska, A., Fornell, J., Suriñach, S., Montserrat, J., Temst, K., Vantomme, A., Baró, M.D., García-Lecina, E., Pellicer, E., Sort, J.
" **INFLUENCE OF THE IRRADIATION TEMPERATURE ON THE SURFACE STRUCTURE AND PHYSICAL/CHEMICAL PROPERTIES OF AN ION-IRRADIATED BULK METALLIC GLASSES** "
JOURNAL OF ALLOYS AND COMPOUNDS. Vol.610 118-125, 2014.

17 - Millán, J., Godignon, P., Perpiñá, X., Pérez-Tomás, A., Rebollo, J.
" **A SURVEY OF WIDE BANDGAP POWER SEMICONDUCTOR DEVICES** "
IEEE TRANSACTIONS ON POWER ELECTRONICS. Vol.29 n° (5), 2155-2163, 2014.
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18 - Navarro, L.A., Perpiñá, X., Godignon, P., Montserrat, J., Banu, V., Vellvehí, M., Jordà, X.
" **THERMOMECHANICAL ASSESSMENT OF DIE-ATTACH MATERIALS FOR WIDE BANDGAP SEMICONDUCTOR DEVICES AND HARSH ENVIRONMENT APPLICATIONS** "

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19 - Ouaida, R., Berthou, M., León, J., Perpiñá, X., Oge, S., Brosselard, P., Joubert, C.
" GATE OXIDE DEGRADATION OF SIC MOSFET IN SWITCHING CONDITIONS "
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20 - Pellegrini, G., Fernández-Martínez, P., Baselga, M., Fleta, C., Flores, D., Greco, V., Hidalgo, S., Mandic, I., Kramberger, G., Quirion, D., Ullán, M.
" TECHNOLOGY DEVELOPMENTS AND FIRST MEASUREMENTS OF LOW GAIN AVALANCHE DETECTORS (LGAD) FOR HIGH ENERGY PHYSICS APPLICATIONS "
NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION A-ACCELERATORS SPECTROMETERS DETECTORS AND ASSOCIATED EQUIPMENT. Vol.765 12-16, 2014.

21 - Perpiñá, X., Jordà, X., León, J., Vellvehí, M., Antón, D., Llorente, S.
" COMPARISON OF TEMPERATURE LIMITS FOR TRENCH SILICON IGBT TECHNOLOGIES FOR MEDIUM POWER APPLICATIONS "
MICROELECTRONICS RELIABILITY. 25th European Symposium on the Reliability of Electron Devices, Failure Physics and Analysis (ESREF), September 29th to October 2nd, 2014, Berlin (Germany). Vol.54 n° (9-10), 1839-1844 SI, 2014.

22 - Perpiñá, X., Jordà, X., Vellvehí, M., Altet, J.
"STUDY OF HEAT SOURCES INTERACTING IN INTEGRATED CIRCUITS BY LASER MIRAGE EFFECT"
APPLIED PHYSICS LETTERS. Vol.105 n° (8), 084101, 2014.

23 - Rius, G., Mestres, N., Tanaka, Y., Miyazaki, H., Eryu, O., Godignon, P.
" FORMATION OF GRAPHENE RIBBONS ONTO ATOMICALLY FLAT 6H-SIC "
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24 - Sadrozinski, H.F.-W., Baselga, M., Ely, S., Fadeyev, V., Galloway, Z., Ngo, J., Parker, C., Schumacher, D., Seiden, A., Zatserklyaniy, A., Cartiglia, N., Pellegrini, G., Fernández-Martínez, P., Greco, V., Hidalgo, S., Quirion, D.
" SENSORS FOR ULTRA-FAST SILICON DETECTORS "
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" OVERLOAD ROBUST IGBT DESIGN FOR SSCB APPLICATION "
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MATERIALS SCIENCE FORUM. 15th International Conference on Silicon Carbide and Related Materials (ICSCRM 2013), SEP 29-OCT 04, 2013, Miyazaki, JAPAN. Vol.778-780 895-898, 2014.

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28 - Vobecky, J., Hazdra, P., Zahlava, V., Mihaila, A., Berthou, M.

" ON-STATE CHARACTERISTICS OF PROTON IRRADIATED 4H-SIC SCHOTTKY DIODE: THE CALIBRATION OF MODEL PARAMETERS FOR DEVICE SIMULATION "

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